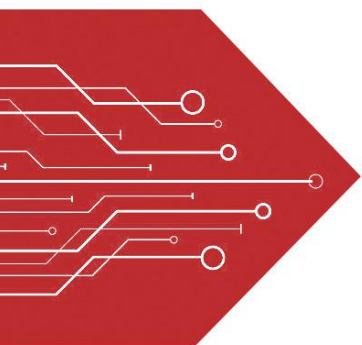


MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT

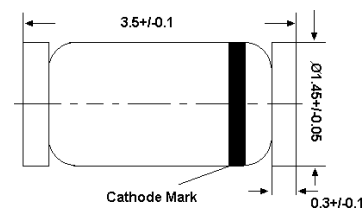


PLED

Product data sheet

Silicon Epitaxial Planar Zener Diodes

in MiniMELF case especially for automatic insertion.
 The Zener voltages are graded according to the international E24 standard. Smaller voltage tolerances and higher Zener voltages are upon request.



Glass case MiniMELF
 Dimensions in mm

SOD-80

REEL SPECIFICATION

P/N	PKG	QTY
BZV55CXXX-MS	SOD-80	2500

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^{\circ}\text{C}$
¹⁾ Valid provided that electrodes are kept at ambient temperature			

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R_{thA}	0.3 ¹⁾	K/mW
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1	V
¹⁾ Valid provided that electrodes are kept at ambient temperature			

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

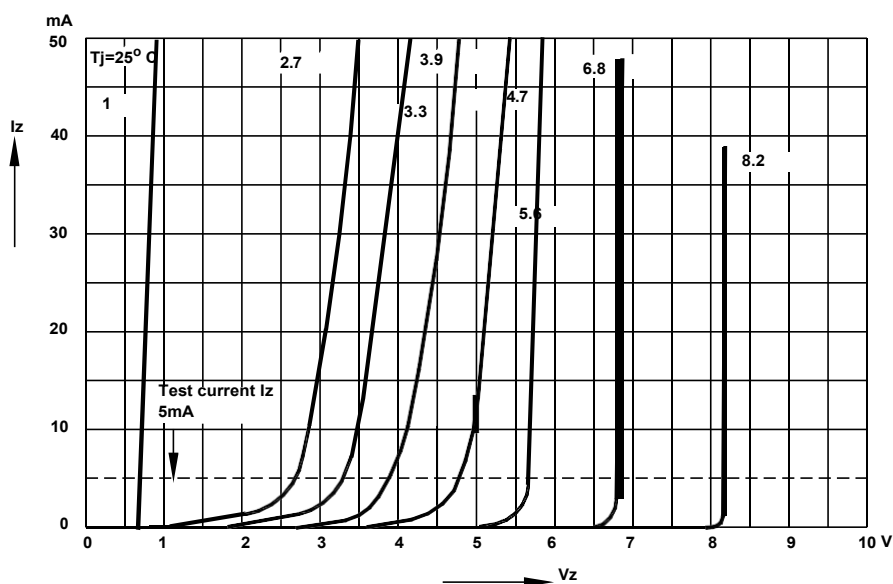
P/N	Zener Voltage Range ¹⁾			Dynamic Resistance			Reverse Leakage Current			Temp. Coefficient of Zener Voltage
	V_{Zno_m}	V_{ZT}	at I_{ZT}	Z_{ZT}	Z_{ZK}	at I_{ZK}	$T_a = 25\text{ }^{\circ}\text{C}$	$T_a = 125\text{ }^{\circ}\text{C}$	at V_R	
	(V)	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (μA)	Max. (μA)	(V)	
BZV55C2V0-MS	2.0	1.8...2.15	5	85	600	1	100	200	1	-0.09...-0.06
BZV55C2V2-MS	2.2	2.08...2.33	5	85	600	1	75	160	1	-0.09...-0.06
BZV55C2V4-MS	2.4	2.28...2.56	5	85	600	1	50	100	1	-0.09...-0.06
BZV55C2V7-MS	2.7	2.5...2.9	5	85	600	1	10	50	1	-0.09...-0.06
BZV55C3V0-MS	3.0	2.8...3.2	5	85	600	1	4	40	1	-0.08...-0.05
BZV55C3V3-MS	3.3	3.1...3.5	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C3V6-MS	3.6	3.4...3.8	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C3V9-MS	3.9	3.7...4.1	5	85	600	1	2	40	1	-0.08...-0.05
BZV55C4V3-MS	4.3	4...4.6	5	75	600	1	1	20	1	-0.06...-0.03
BZV55C4V7-MS	4.7	4.4...5	5	60	600	1	0.5	10	1	-0.05...+0.02
BZV55C5V1-MS	5.1	4.8...5.4	5	35	550	1	0.1	2	1	-0.02...+0.02
BZV55C5V6-MS	5.6	5.2...6	5	25	450	1	0.1	2	1	-0.05...+0.05
BZV55C6V2-MS	6.2	5.8...6.6	5	10	200	1	0.1	2	2	0.03...0.06
BZV55C6V8-MS	6.8	6.4...7.2	5	8	150	1	0.1	2	3	0.03...0.07
BZV55C7V5-MS	7.5	7...7.9	5	7	50	1	0.1	2	5	0.03...0.07
BZV55C8V2-MS	8.2	7.7...8.7	5	7	50	1	0.1	2	6.2	0.03...0.08
BZV55C9V1-MS	9.1	8.5...9.6	5	10	50	1	0.1	2	6.8	0.03...0.09
BZV55C10-MS	10	9.4...10.6	5	15	70	1	0.1	2	7.5	0.03...0.1
BZV55C11-MS	11	10.4...11.6	5	20	70	1	0.1	2	8.2	0.03...0.11
BZV55C12-MS	12	11.4...12.7	5	20	90	1	0.1	2	9.1	0.03...0.11
BZV55C13-MS	13	12.4...14.1	5	26	110	1	0.1	2	10	0.03...0.11
BZV55C15-MS	15	13.8...15.6	5	30	110	1	0.1	2	11	0.03...0.11
BZV55C16-MS	16	15.3...17.1	5	40	170	1	0.1	2	12	0.03...0.11
BZV55C18-MS	18	16.8...19.1	5	50	170	1	0.1	2	13	0.03...0.11
BZV55C20-MS	20	18.8...21.2	5	55	220	1	0.1	2	15	0.03...0.11
BZV55C22-MS	22	20.8...23.3	5	55	220	1	0.1	2	16	0.04...0.12
BZV55C24-MS	24	22.8...25.6	5	80	220	1	0.1	2	18	0.04...0.12
BZV55C27-MS	27	25.1...28.9	5	80	220	1	0.1	2	20	0.04...0.12
BZV55C30-MS	30	28...32	5	80	220	1	0.1	2	22	0.04...0.12
BZV55C33-MS	33	31...35	5	80	220	1	0.1	2	24	0.04...0.12
BZV55C36-MS	36	34...38	5	80	220	1	0.1	2	27	0.04...0.12
BZV55C39-MS	39	37...41	2.5	90	500	0.5	0.1	5	30	0.04...0.12
BZV55C43-MS	43	40...46	2.5	90	500	0.5	0.1	5	33	0.04...0.12
BZV55C47-MS	47	44...50	2.5	110	600	0.5	0.1	5	36	0.04...0.12
BZV55C51-MS	51	48...54	2.5	125	700	0.5	0.1	10	39	0.04...0.12
BZV55C56-MS	56	52...60	2.5	135	700	0.5	0.1	10	43	0.04...0.12
BZV55C62-MS	62	58...66	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
BZV55C68-MS	68	64...72	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
BZV55C75-MS	75	70...79	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

¹⁾ Tested with pulses $t_p = 20\text{ms}$.

²⁾ The ZMM1 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be "F" instead of "Z". Connect the cathode electrode to the negative pole.

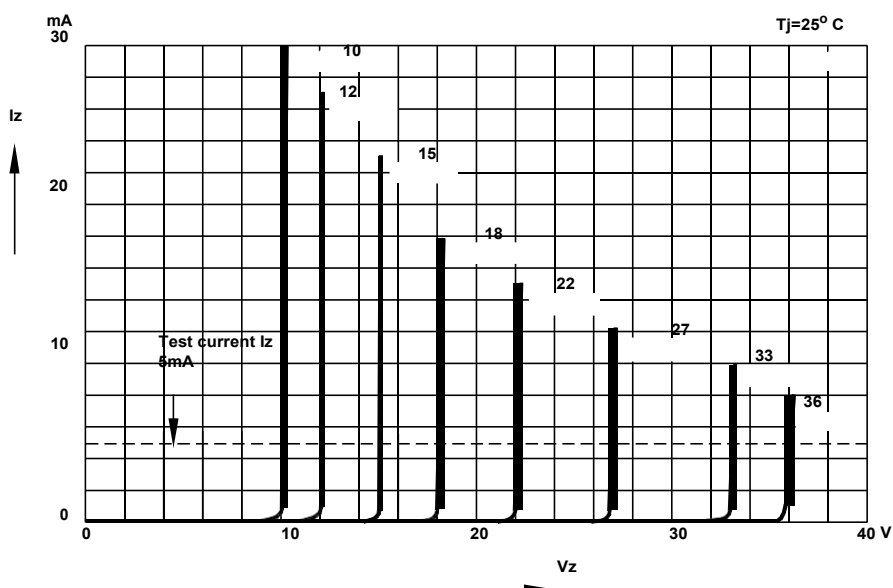
Breakdown characteristics

$T_j = \text{constant (pulsed)}$

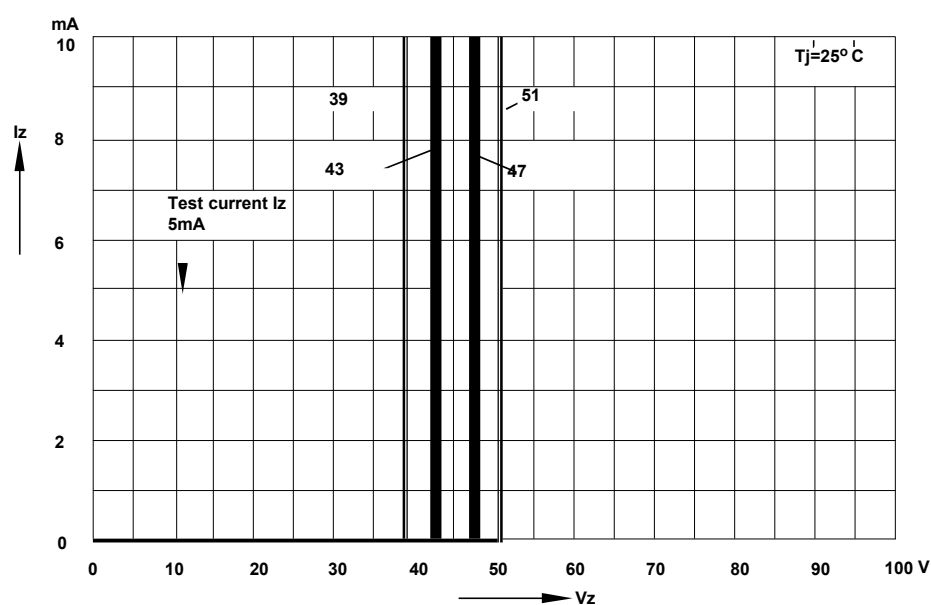


Breakdown characteristics

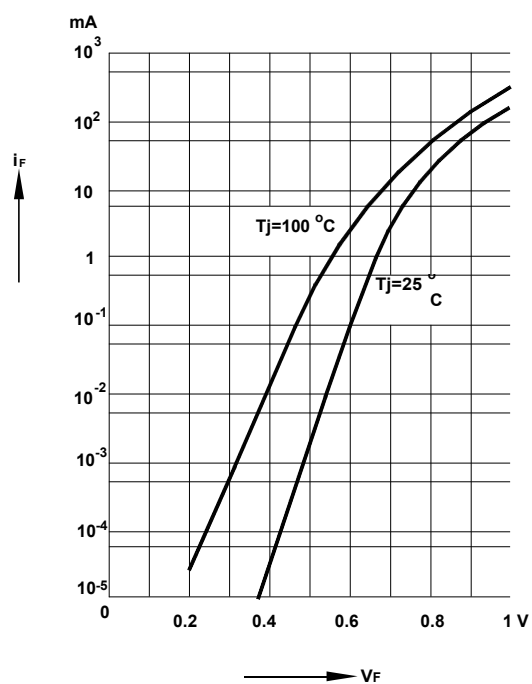
$T_j = \text{constant (pulsed)}$



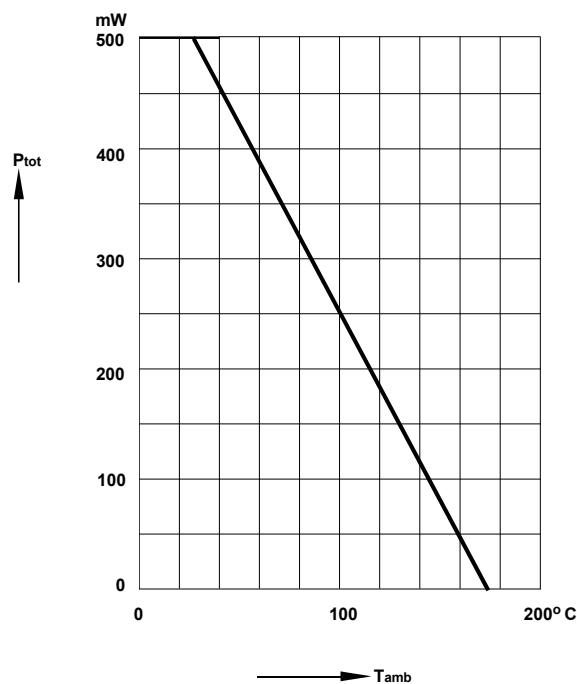
Breakdown characteristics
 $T_J = \text{constant (pulsed)}$

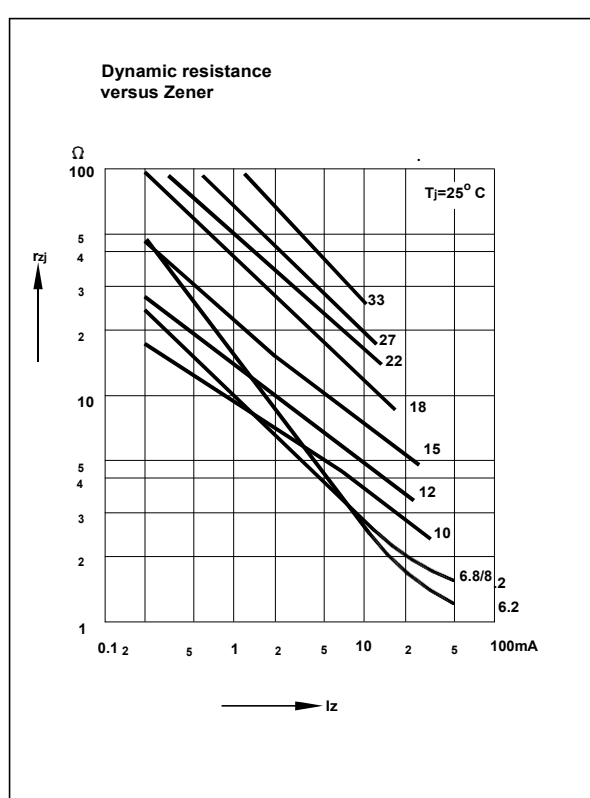
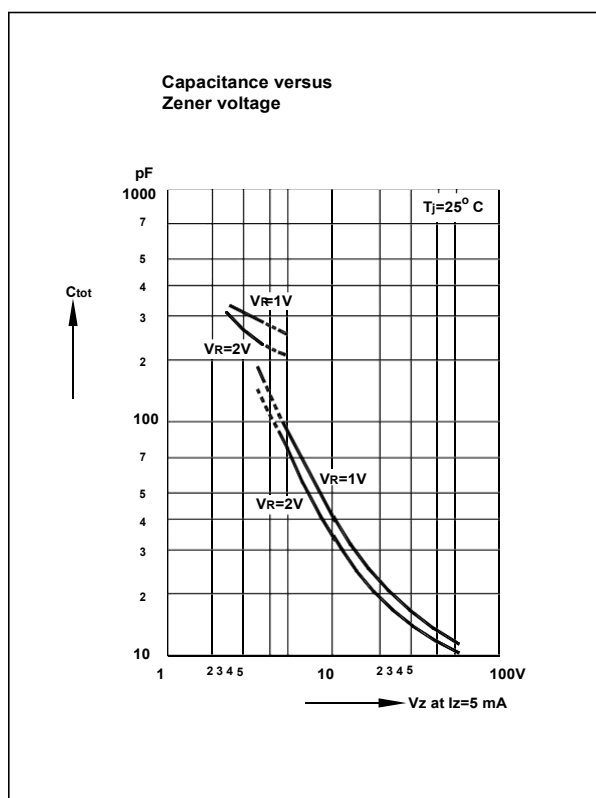
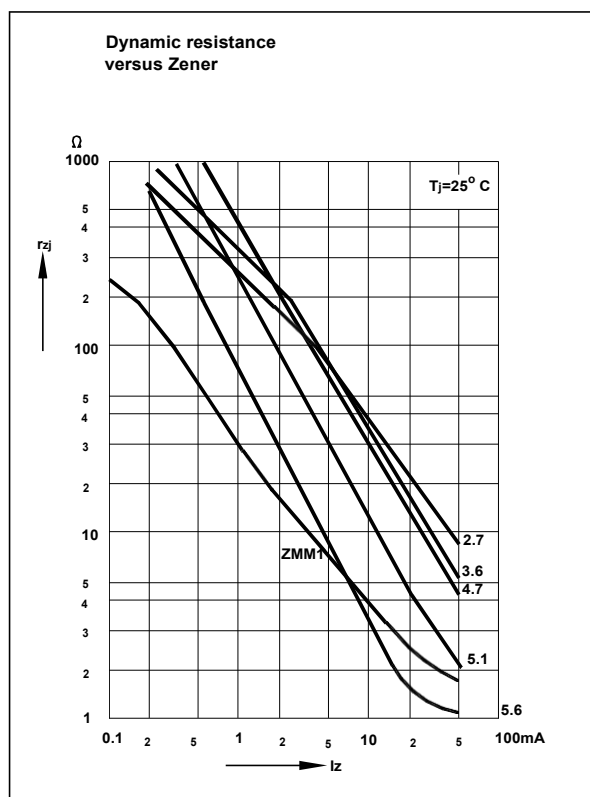
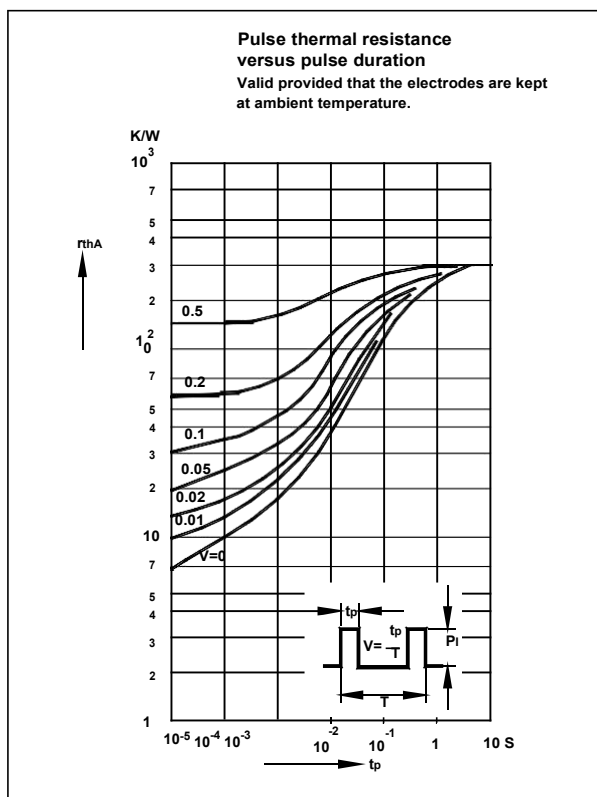


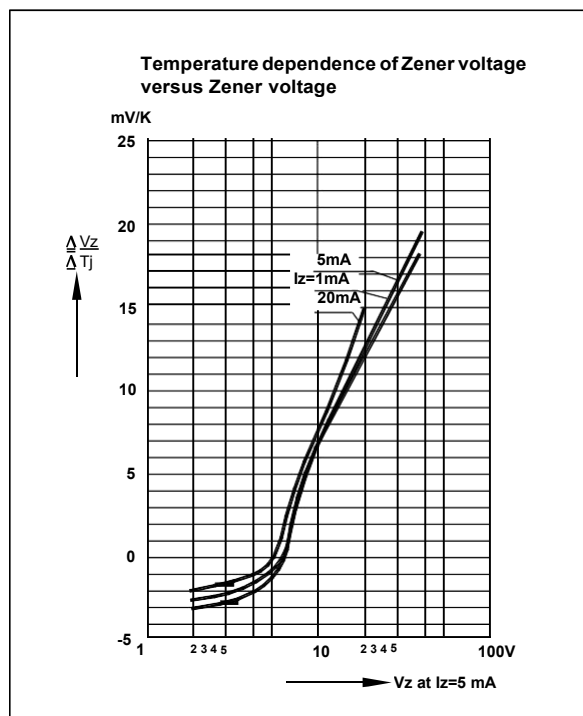
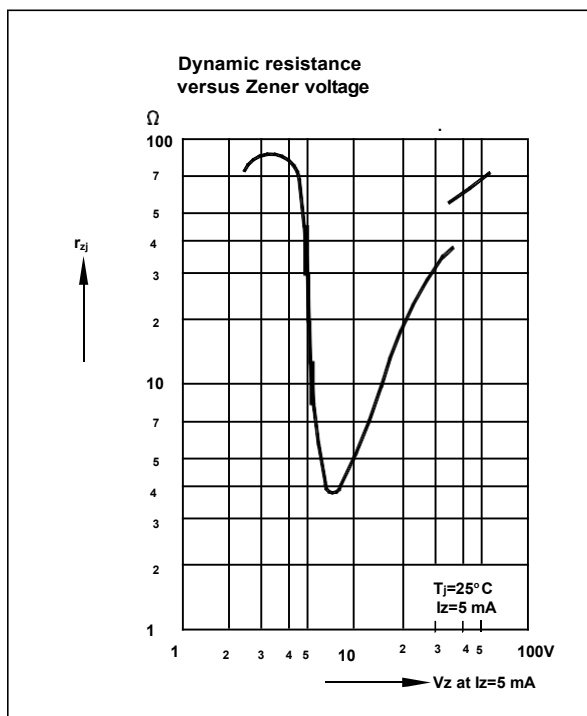
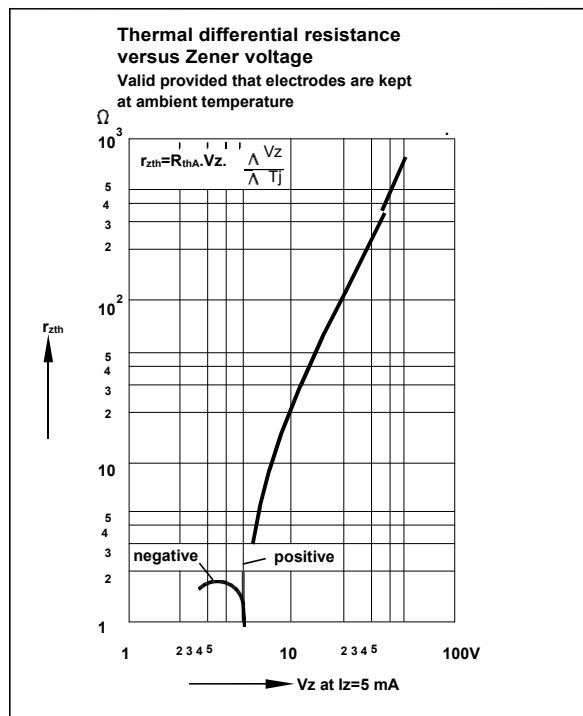
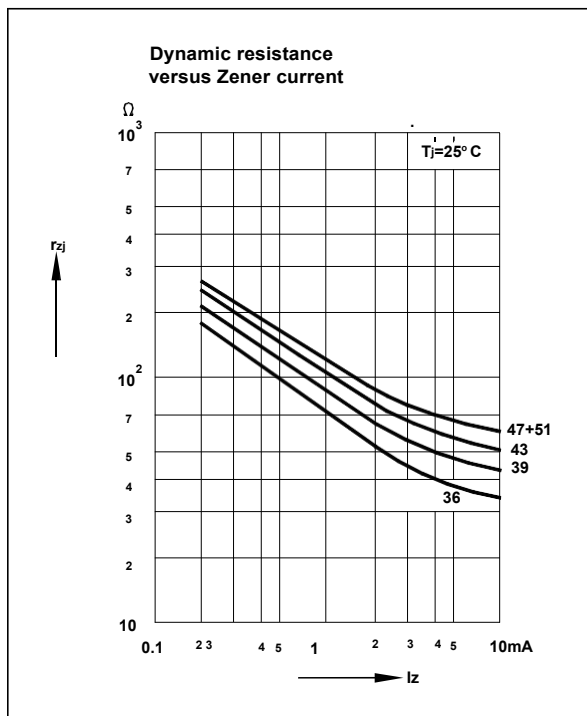
Forward characteristics



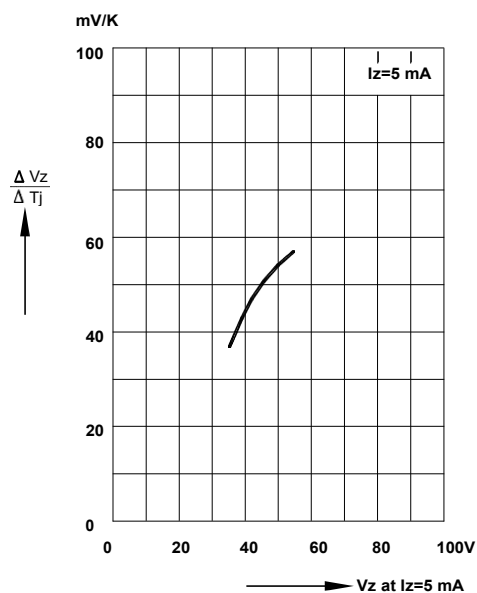
Admissible power dissipation versus ambient temperature
Valid provided that electrodes are kept at ambient temperature.



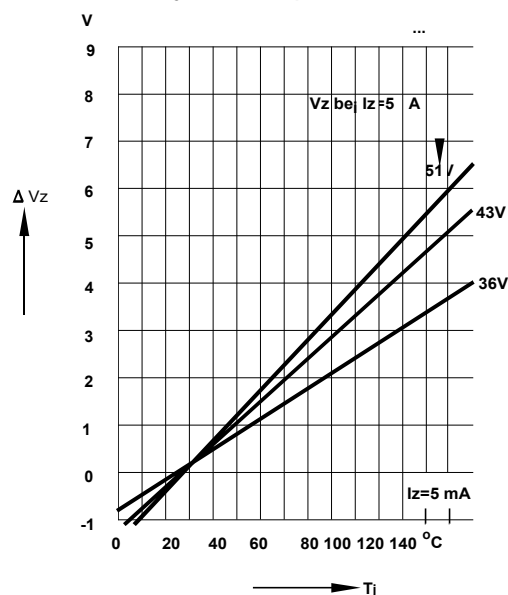




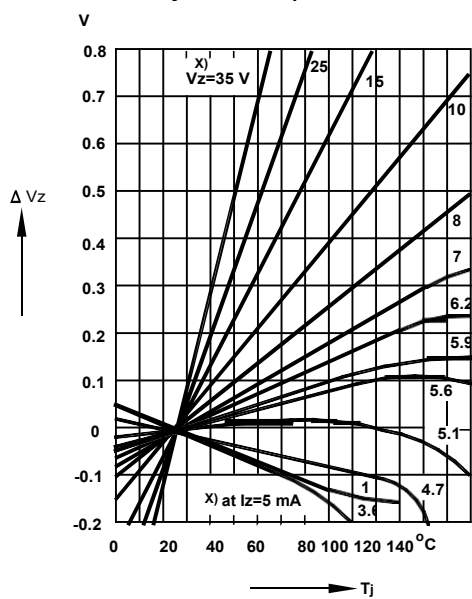
Temperature dependence of Zener voltage
versus Zener voltage



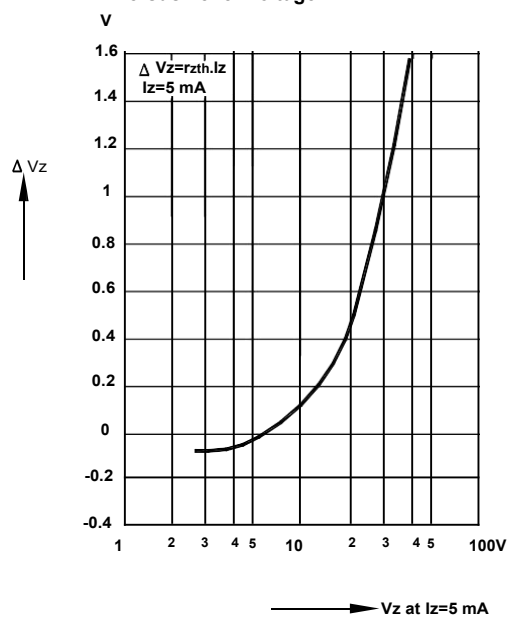
Change of Zener voltage
versus junction temperature

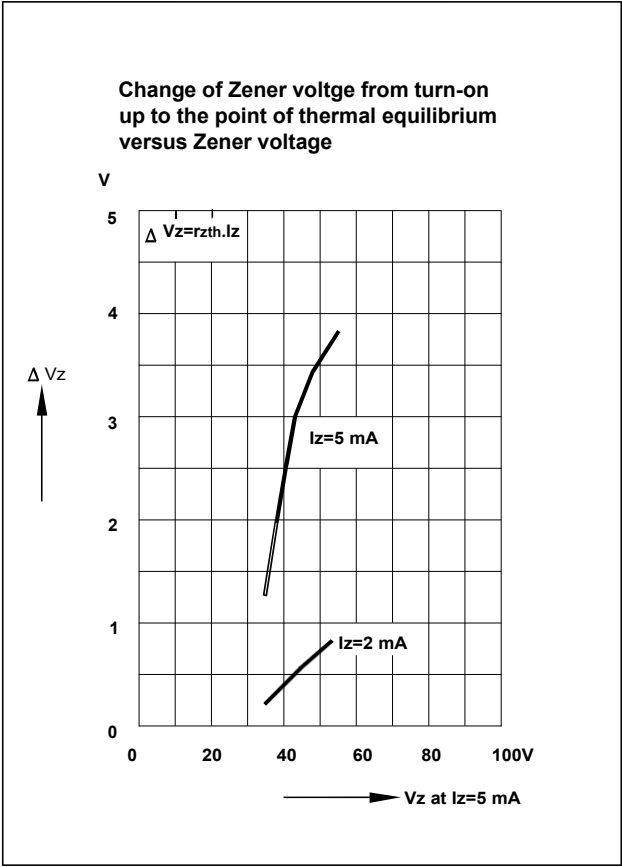


Change of Zener voltage
versus junction temperature



Change of Zener voltage from turn-on
up to the point of thermal equilibrium
versus Zener voltage





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